

SOT223 PNP SILICON PLANAR MEDIUM POWER HIGH GAIN TRANSISTOR

FZT788B

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FEATURES

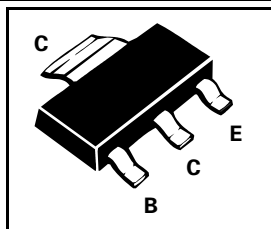
- * Low equivalent on-resistance; $R_{CE(sat)}$ **93mΩ at 3A**
- * Gain of 300 at $I_C=2$ Amps and Very low saturation voltage

APPLICATIONS

- * Battery powered circuits

COMPLEMENTARY TYPE – FZT688B

PARTMARKING DETAIL – FZT788B



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-15	V
Collector-Emitter Voltage	V_{CEO}	-15	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-8	A
Continuous Collector Current	I_C	-3	A
Power Dissipation at $T_{amb}=25^\circ\text{C}$	P_{tot}	2	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-15			V	$I_C=-100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-15			V	$I_C=-10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E=-100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			-0.1	μA	$V_{CE}=-10\text{V}$
Emitter Cut-Off Current	I_{EBO}			-0.1	μA	$V_{EB}=-4\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.15 -0.25 -0.45 -0.5	V	$I_C=-0.5\text{A}, I_B=-2.5\text{mA}^*$ $I_C=-1\text{A}, I_B=-5\text{mA}^*$ $I_C=-2\text{A}, I_B=-10\text{mA}^*$ $I_C=-3\text{A}, I_B=-50\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$			-0.9	V	$I_C=-1\text{A}, I_B=-5\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-0.75		V	$I_C=-1\text{A}, V_{CE}=-2\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	500 400 300 150		1500		$I_C=-10\text{mA}, V_{CE}=-2\text{V}^*$ $I_C=-1\text{A}, V_{CE}=-2\text{V}^*$ $I_C=-2\text{A}, V_{CE}=-2\text{V}^*$ $I_C=-6\text{A}, V_{CE}=-2\text{V}^*$
Transition Frequency	f_T	100			MHz	$I_C=-50\text{mA}, V_{CE}=-5\text{V}$ $f=50\text{MHz}$
Input Capacitance	C_{ibo}		225		pF	$V_{EB}=-0.5\text{V}, f=1\text{MHz}$
Output Capacitance	C_{obo}		25		pF	$V_{CE}=-10\text{V}, f=1\text{MHz}$
Switching Times	t_{on} t_{off}		35 400		ns ns	$I_C=-500\text{mA}, I_{B1}=-50\text{mA}$ $I_{B2}=-50\text{mA}, V_{CC}=-10\text{V}$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$
Spice parameter data is available upon request for this device

TYPICAL CHARACTERISTICS

